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PATENTS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Meikei leong, et al.
Application No: 10/647395
Patent No: 6,815,278

Docket: 16527
Dated: April 8, 2005

Issued: November 9, 2004

**For: ULTRA-THIN SILICON-ON-INSULATOR AND
STRAINED-SILICON-DIRECT-ON-
INSULATOR WITH HYBIRD CRYSTAL
ORIENTATIONS**

**Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450**

REQUEST FOR CERTIFICATE OF CORRECTION

Sir:

**It appearing that errors have been introduced in the course of
printing the Patent issued in the above application,
it is respectfully requested that the Commissioner issue a Certificate of Correction
in the following respects:**

Column 12, Line 21 "stained" should read -- strained --

**Column 11, Line 54 "the method of claim wherein" should read -- the
method of claim 1 wherein --**

Column 12, Line 30 " Insert missing paragraph"

**--forming an insulator layer on the structure and bonding the insulator to a
handling wafer; selectively removing the carrier wafer, first semiconductor
layer and the second
semiconductor layer to expose the second graded SiGe alloy; and --**

It is further noted that additional errors typographical in nature are incorporated into the printed specification, but are believed to be satisfactorily clear in the context and accordingly it is simply requested that this paper be made of record in the file for such clarification as may be appropriate. They are as follows:

Column 3, Line 44 "stained" should read -- strained --

Column 3, Line 66 "stained" should read -- strained --

Column 12, Line 9 "nFET the (100) suface" should read -- nFET on the (100) surface --

Respectfully submitted,



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**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

PATENT NO : 6,815,278
DATED : November 9, 2004
INVENTOR(S) : Melkel leong, et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 12, Line 21 "stained" should read -- strained --

Column 11, Line 54 "the method of claim wherein" should read -- the method of claim 1 wherein --

Column 12, Line 30 " Insert missing paragraph"

--forming an insulator layer on the structure and bonding the insulator to a handling wafer;
selectively removing the carrier wafer, first semiconductor layer and the second
semiconductor layer to expose the second graded SiGe alloy; and --

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PATENT NO. 6,815,278

No. of additional copies

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